

Features

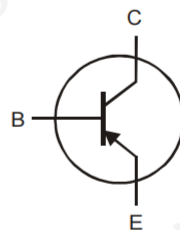
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching



SOT23

Mechanical Data

- Case: SOT23
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Copper leadframe.
Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)



Device Symbol

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-80	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Continuous Collector Current	I _C	-1	A
Peak Pulse Collector Current	I _{CM}	-2	A
Base Current (DC)	I _B	-300	mA
Peak Base Current	I _{BM}	-1	A

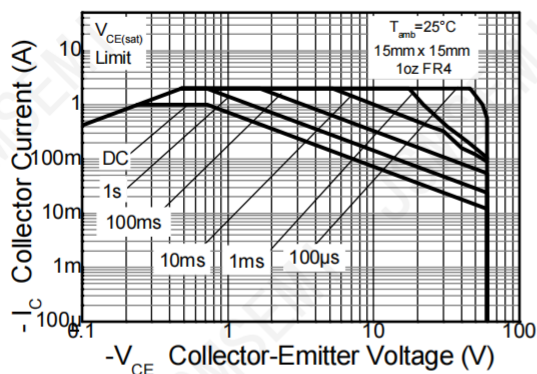
Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	725	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	172	°C/W
Thermal Resistance, Junction to Ambient Air (Note 4)	R _{θJA}	79	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

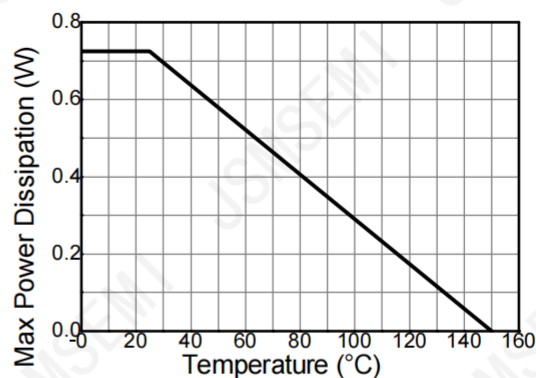
Notes: 4. Operated under pulsed conditions: pulse width ≤100ms, duty cycle ≤ 0.25.
5. Device mounted on 15mm x 15mm x1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.



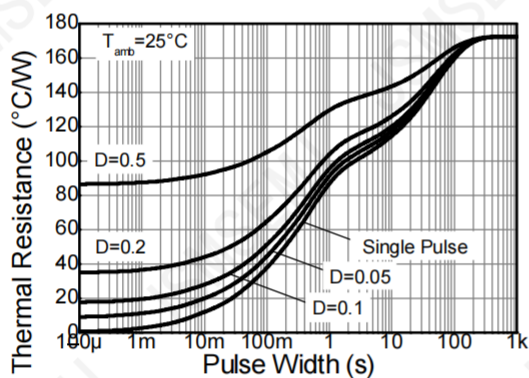
Thermal Characteristics



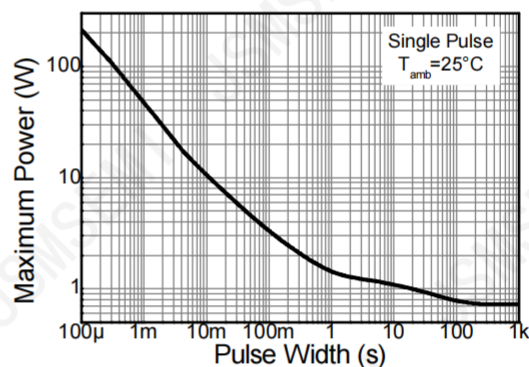
Safe Operating Area



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation



Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{CBO}	-80	—	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 6)	BV _{CEO}	-60	—	—	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	—	—	V	I _E = -100μA
Collector-Base Cutoff Current	I _{CBO}	—	—	-100	nA	V _{CB} = -20V, I _E = 0
		—	—	-50	μA	V _{CB} = -20V, I _E = 0, T _A = 150°C
Emitter-Base Cutoff Current	I _{EBO}	—	—	-100	nA	V _{EB} = -5V, I _C = 0
DC Current Gain (Note 6)	h _{FE}	200	—	—	—	V _{CE} = -5V, I _C = -1mA
		150	—	—		V _{CE} = -5V, I _C = -500mA
		100	—	—		V _{CE} = -5V, I _C = -1A
Collector-Emitter Saturation Voltage (Note 6)	V _{CE(sat)}	—	—	-175	mV	I _C = -100mA, I _B = -1mA
		—	—	-180		I _C = -500mA, I _B = -50mA
		—	—	-340		I _C = -1A, I _B = -100mA
Equivalent On-Resistance	R _{CE(sat)}	—	—	340	mΩ	I _E = -1A, I _B = -100mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	—	—	-1.1	V	I _C = -1A, I _B = -50mA
Base-Emitter Turn-on Voltage	V _{BE(on)}	—	—	-0.9	V	V _{CE} = -5V, I _C = -1A
Transition Frequency	f _T	150	—	—	MHz	V _{CE} = -10V, I _C = -50mA, f = 100MHz
Output Capacitance	C _{ob}	—	—	15	pF	V _{CB} = -10V, f = 1MHz
Turn-On Time	t _{on}	—	75	—	ns	V _{CC} = -10V, I _C = -0.5A, I _{B1} = I _{B2} = -25mA
Delay Time	t _d	—	35	—	ns	
Rise Time	t _r	—	40	—	ns	
Turn-Off Time	t _{off}	—	265	—	ns	
Storage Time	t _s	—	230	—	ns	
Fall Time	t _f	—	35	—	ns	

Notes 6. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

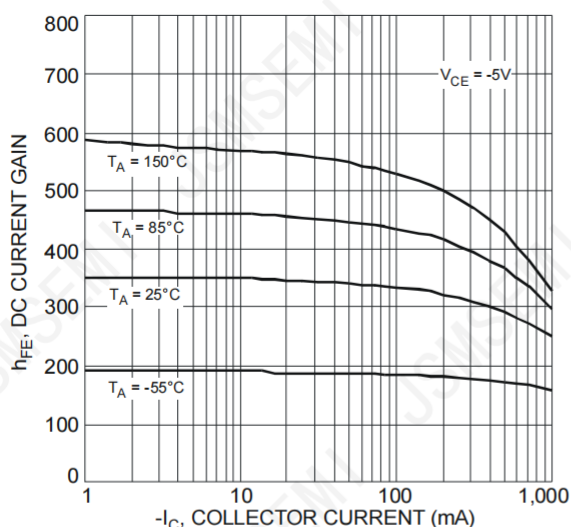


Fig. 5 Typical DC Current Gain vs. Collector Current

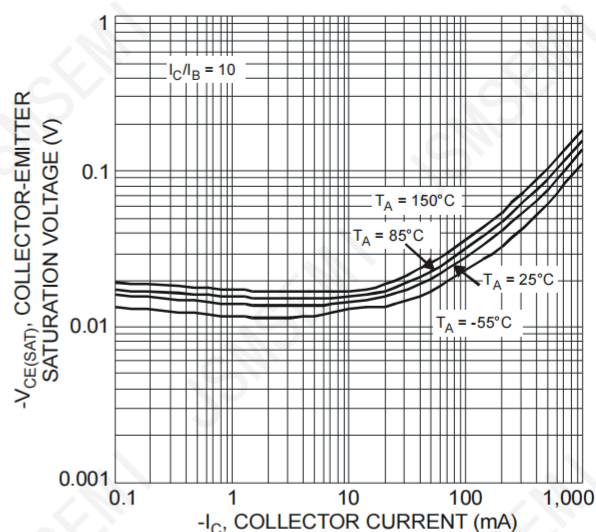


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

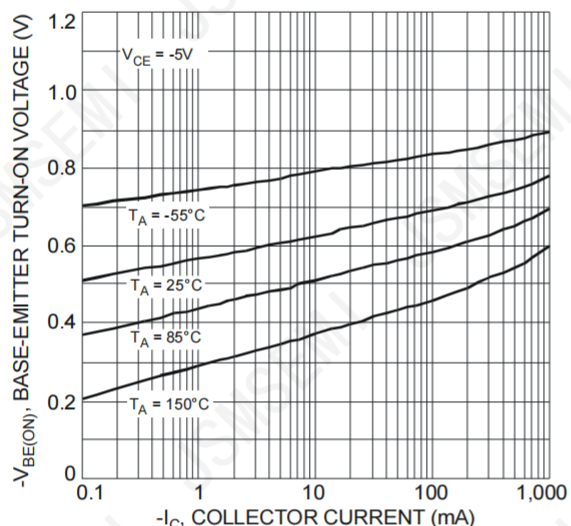


Fig. 7 Typical Base-Emitter Turn-On Voltage vs. Collector Current

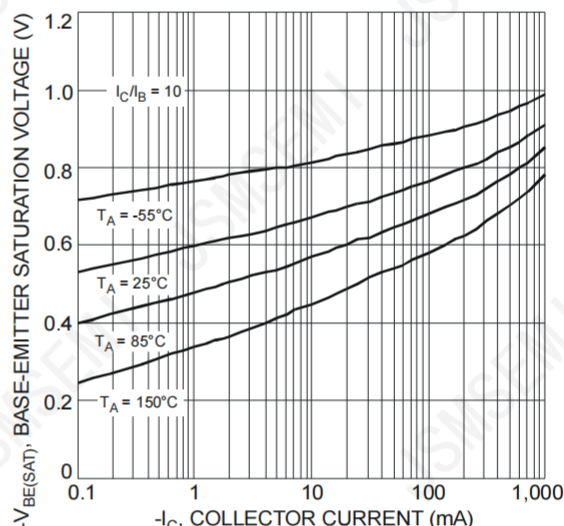


Fig. 8 Typical Base-Emitter Saturation Voltage vs. Collector Current

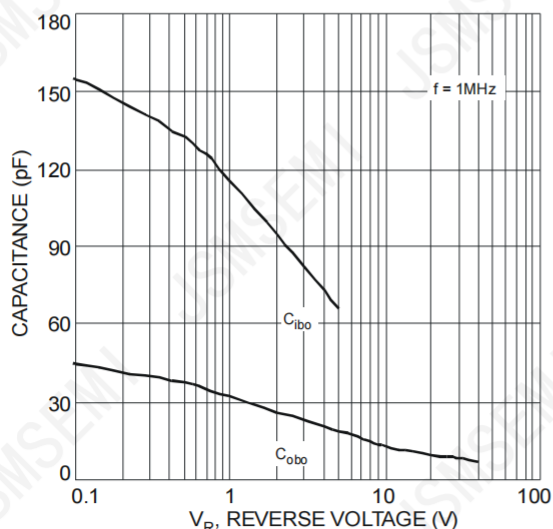
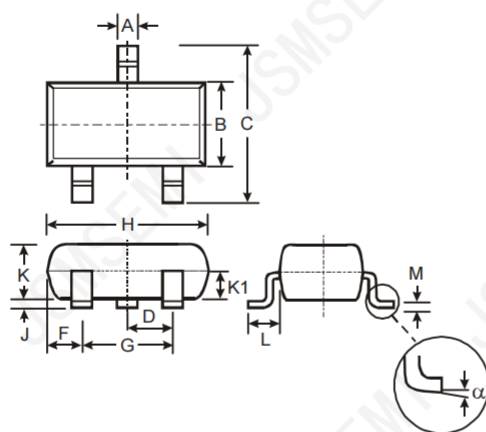


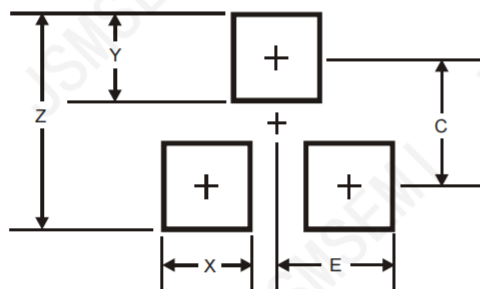
Fig. 9 Typical Capacitance Characteristics

Package Outline Dimensions



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

Revision History

Rev.	Change	Date
V1.0	Initial version	2/23/2024

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